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CLAIMS

1. A process for forming an underlying film,
comprising: irradiating the surface of an insulating film
disposed on an electronic device substrate with plasma
5 based on a process gas comprising at least an oxygen
atom-containing gas, to thereby form an underlying film
at the interface between the insulating film and the
electronic device substrate.

2. A process for forming an underlying film
10 according to claim 1, wherein the insulating film is a
film comprising a high-k (high-dielectric constant)
material.

3. A process for forming an underlying film
according to claim 1 or 2, wherein the plasma is plasma
15 containing oxygen radicals.

4. A process for forming an underlying film
according to any one of claims 1 to 3, wherein the
underlying film is an oxide film.

5. A process for forming an underlying film
20 according to any one of claims 1 to 4, wherein the plasma
is plasma based on a plane antenna member (RLSA).

6. An electronic device material, comprising: an
electronic device substrate, an underlying film disposed
on the substrate, and an insulating film disposed on the
25 underlying film,

wherein the underlying film is a film
which has been formed by supplying plasma from the
insulating layer side.

7. The electronic device material according to claim
30 6, wherein the insulating film is a film comprising a
high-k (high-dielectric constant) material.